

Product Summary

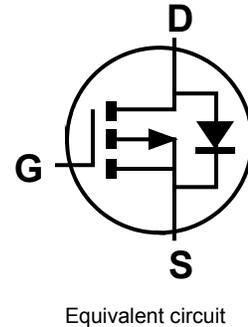
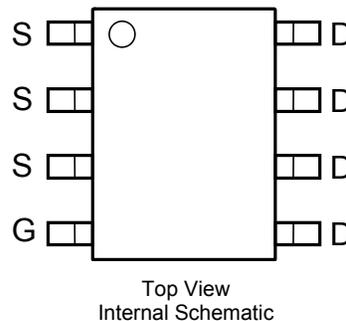
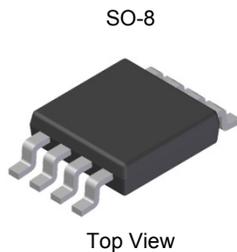
| $V_{(BR)DSS}$ | $R_{DS(ON)}$ max | I_D max $T_A = +25^\circ\text{C}$ |
|---------------|--|--|
| -30V | 40m Ω @ $V_{GS} = -4.5\text{V}$ | -6.5A |
| | 70m Ω @ $V_{GS} = -2.5\text{V}$ | -5.0A |

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters



Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

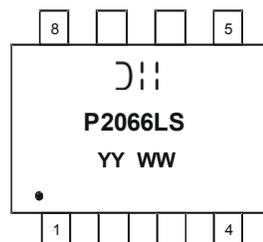
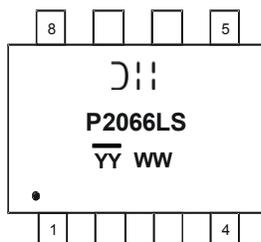
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.074g (approximate)

Ordering Information (Note 4)

| Part Number | Case | Packaging |
|---------------|------|------------------|
| DMP2066LSS-13 | SO-8 | 2500/Tape & Reel |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



- ⌋⌋⌋ = Manufacturer's Marking
- P2066LS = Product Type Marking Code
- YYWW = Date Code Marking
- YY or \overline{YY} = Year (ex: 13 = 2013)
- WW = Week (01 - 53)
- YY = Date Code Marking for SAT (Shanghai Assembly/ Test site)
- \overline{YY} = Date Code Marking for CAT (Chengdu Assembly/ Test site)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Units |
|--|--------------|------------------------|------------------|-------|-------|
| Drain-Source Voltage | | | V _{DSS} | -20 | V |
| Gate-Source Voltage | | | V _{GSS} | ±12 | V |
| Drain Current (Note 5) | Steady State | T _A = +25°C | I _D | -6.5 | A |
| | | T _A = +70°C | | -5.2 | |
| Pulsed Drain Current (10µs pulse, duty cycle = 1%) | | | I _{DM} | -26 | A |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|--|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 5) | P _D | 2.5 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | R _{θJA} | 50 | °C/W |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C |

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|---|---------------------|------|-------|------|------|---|
| OFF CHARACTERISTICS (Note 6) | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | -20 | — | — | V | V _{GS} = 0V, I _D = -250µA |
| Zero Gate Voltage Drain Current | I _{DSS} | — | — | -1 | µA | V _{DS} = -20V, V _{GS} = 0V |
| Gate-Source Leakage | I _{GSS} | — | — | ±100 | nA | V _{GS} = ±12V, V _{DS} = 0V |
| ON CHARACTERISTICS (Note 6) | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | -0.6 | — | -1.2 | V | V _{DS} = V _{GS} , I _D = -250µA |
| Static Drain-Source On-Resistance | R _{DS(on)} | — | — | 40 | mΩ | V _{GS} = -4.5V, I _D = -5.8A |
| | | — | — | 70 | | V _{GS} = -2.5V, I _D = -3.8A |
| Forward Transconductance | g _{fs} | — | 9 | — | S | V _{DS} = -10V, I _D = -4.6A |
| Diode Forward Voltage | V _{SD} | -0.5 | -0.72 | -1.4 | V | V _{GS} = 0V, I _S = -2.1A |
| DYNAMIC CHARACTERISTICS (Note 7) | | | | | | |
| Input Capacitance | C _{iss} | — | 820 | — | pF | V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz |
| Output Capacitance | C _{oss} | — | 200 | — | pF | |
| Reverse Transfer Capacitance | C _{rss} | — | 160 | — | pF | |
| Gate Resistance | R _g | — | 10.4 | — | Ω | V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz |
| Total Gate Charge | Q _g | — | 14.4 | — | nC | V _{DS} = -10V, V _{GS} = -4.5V I _D = -4.5A |
| Gate-Source Charge | Q _{gs} | — | 2.6 | — | | |
| Gate-Drain Charge | Q _{gd} | — | 2.7 | — | | |
| Turn-On Delay Time | t _{D(on)} | — | 13.7 | — | ns | V _{DD} = -10V, V _{GS} = -4.5V, R _G = 6Ω, R _L = 10Ω, I _D = -1A |
| Turn-On Rise Time | t _r | — | 14.0 | — | | |
| Turn-Off Delay Time | t _{D(off)} | — | 79.1 | — | | |
| Turn-Off Fall Time | t _f | — | 35.5 | — | | |

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

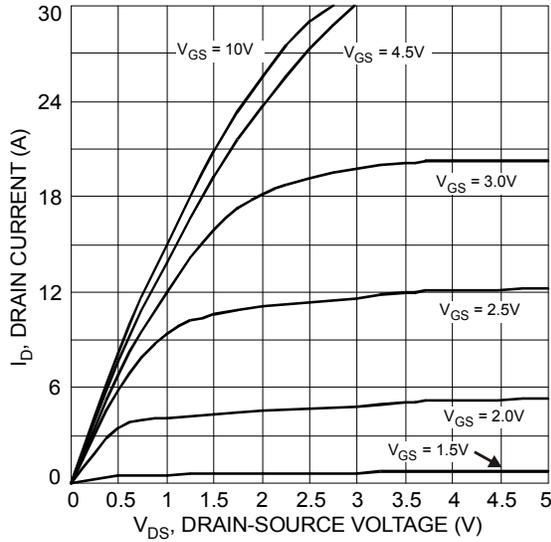


Fig. 1 Typical Output Characteristic

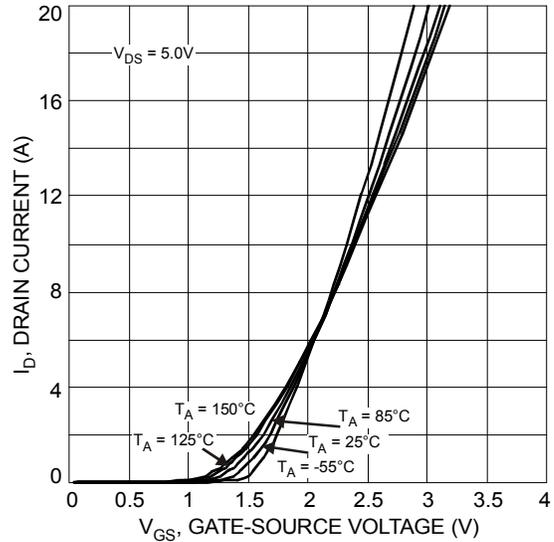


Fig. 2 Typical Transfer Characteristic

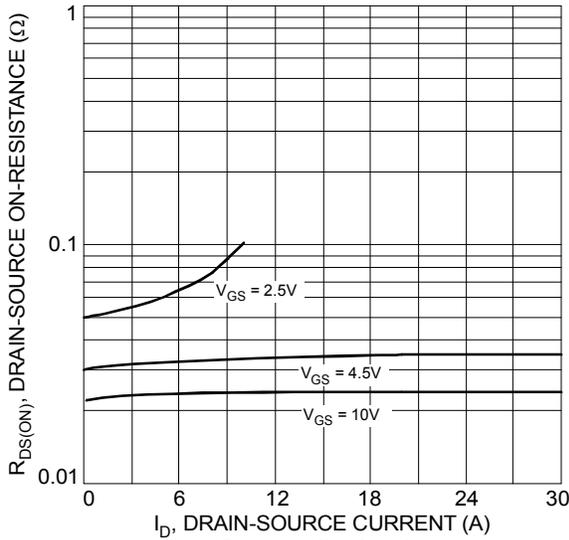


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

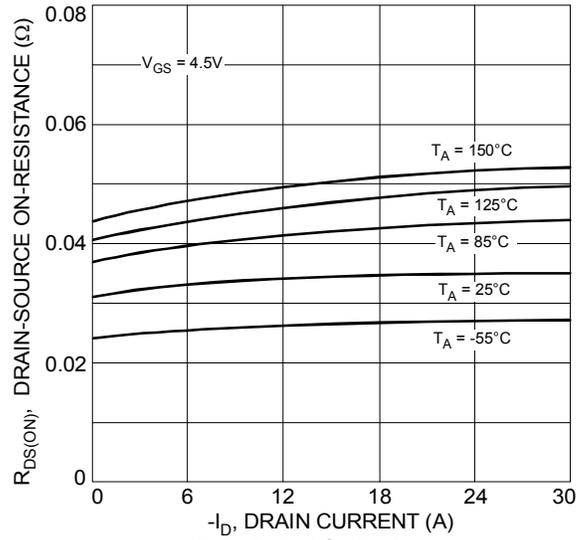


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

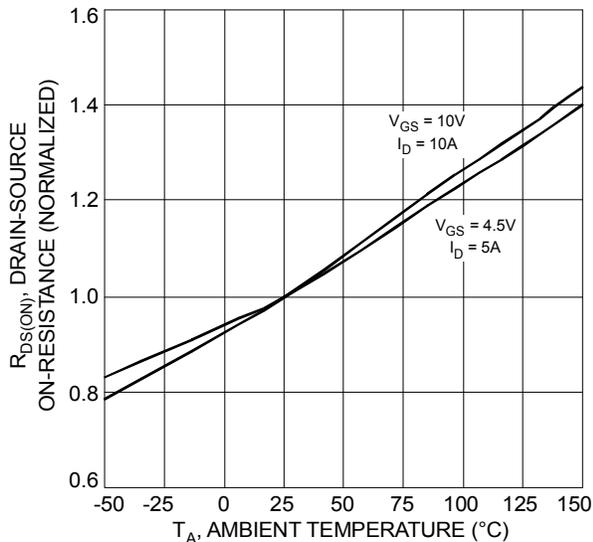


Fig. 5 Normalized On-Resistance vs. Ambient Temperature

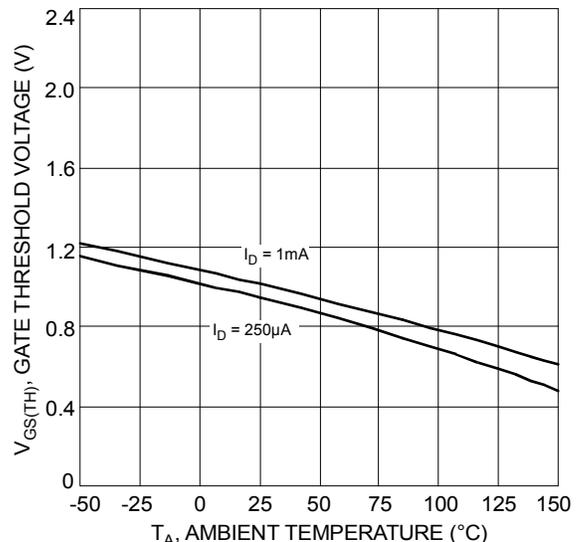


Fig. 6 Gate Threshold Variation vs. Ambient Temperature

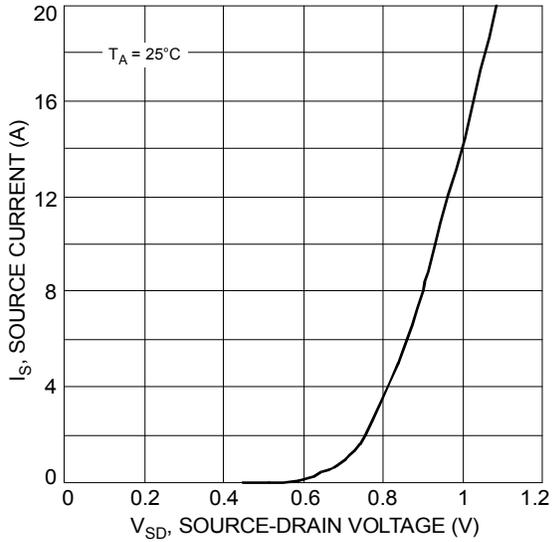


Fig. 7 Diode Forward Voltage vs. Current

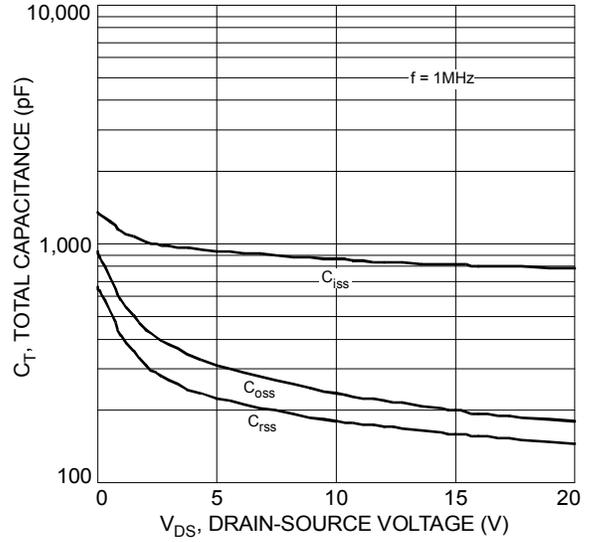


Fig. 8 Typical Total Capacitance

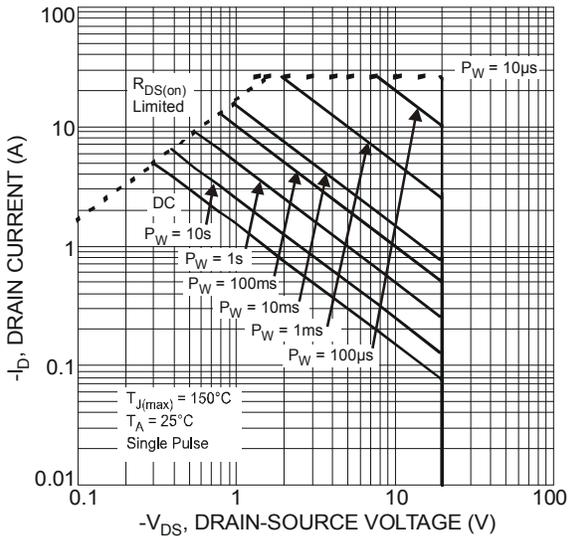
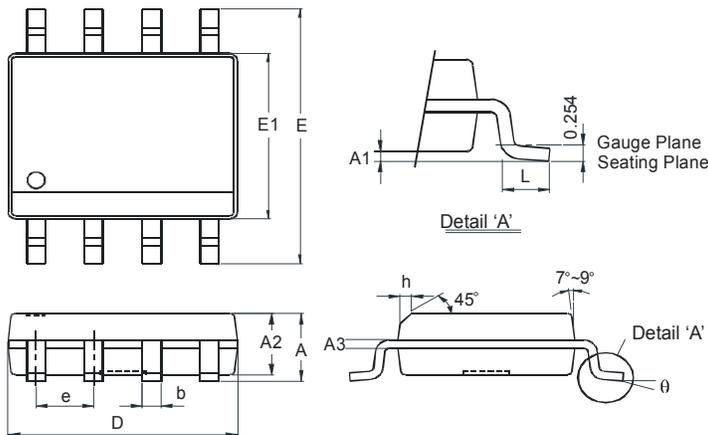


Fig. 9 SOA, Safe Operation Area

Package Outline Dimensions

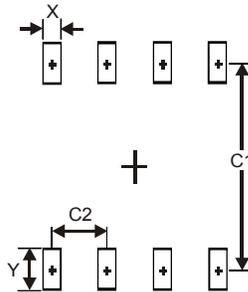
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



| SO-8 | | |
|----------------------|----------|------|
| Dim | Min | Max |
| A | - | 1.75 |
| A1 | 0.10 | 0.20 |
| A2 | 1.30 | 1.50 |
| A3 | 0.15 | 0.25 |
| b | 0.3 | 0.5 |
| D | 4.85 | 4.95 |
| E | 5.90 | 6.10 |
| E1 | 3.85 | 3.95 |
| e | 1.27 Typ | |
| h | - | 0.35 |
| L | 0.62 | 0.82 |
| θ | 0° | 8° |
| All Dimensions in mm | | |

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| X | 0.60 |
| Y | 1.55 |
| C1 | 5.4 |
| C2 | 1.27 |

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